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FCA22N60N

May 2014

N-Channel SupreMOS[®] MOSFET 600 V, 22 A, 165 m Ω

Features

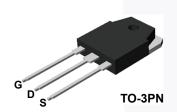
- BV_{DSS} > 650 V @ T_J = 150°C
- $R_{DS(on)}$ = 140 $m\Omega$ (Typ.) @ V_{GS} = 10 V, I_D = 11 A
- Ultra Low Gate Charge (Typ. Q_g = 45 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 196.4 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

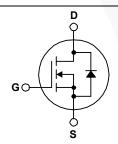
Application

- PDP TV
- · Solar Inverter
- AC-DC Power Supply

Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest Rsp on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.





MOSFET Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol			FCA22N60N	Unit		
V _{DSS}	Drain to Source Voltage			600	V	
V _{GSS}	Gate to Source Voltage			±30	V	
	Drain Current	- Continuous (T _C = 25°C)	7	22	_	
ID	Drain Current	- Continuous (T _C = 100°C)		13.8	A	
I _{DM}	Drain Current	- Pulsed	- Pulsed (Note 1)		Α	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		(Note 2)	672	mJ	
I _{AR}	Avalanche Current		(Note 1)	7.3	Α	
E _{AR}	Repetitive Avalanche Energy (f		(Note 1)	2.75	mJ	
dv/dt	MOSFET dv/dt			100	V/ns	
av/at	Peak Diode Recovery dv/d	t	(Note 3)	20	V/IIS	
D	Dawer Dissination	$(T_C = 25^{\circ}C)$		205	W	
P _D Power Dissipation	- Derate Above 25°C		1.64	W/°C		
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperatu	re for Soldering, 1/8" from Case for 5 Seco	nds	300	°C	

Thermal Characteristics

Symbol	Parameter FCA22		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.61	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCA22N60N	FCA22N60N	TO-3PN	Tube	N/A	N/A	30 units

Test Conditions

Min.

Тур.

Max.

Unit

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted. Parameter

Off Chara	acteristics					
D\/	Drain to Source Breakdown Voltage	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C}$	600	-	-	V
BV _{DSS} Drain to Source Breakdown Voltage	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 150^{\circ}\text{C}$	650	-	-	, v	
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C	-	0.68	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 480 V, V _{GS} = 0 V	-	-	10	μА
DSS	Zero Gate Voltage Diam Guirent	$V_{DS} = 480 \text{ V}, T_{J} = 125^{\circ}\text{C}$	-	-	100	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±50 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

Symbol

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2.0	3	4.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 11 \text{ A}$	-	0.140	0.165	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_{D} = 11 \text{ A}$	-	22	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V = 400 V V = 0 V	-	1950	-	pF
C _{oss}	Output Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz		75.9	-	pF
C _{rss}	Reverse Transfer Capacitance			3	-	pF
C _{oss}	Output Capacitance	V _{DS} = 380 V, V _{GS} = 0 V, f = 1 MHz	- \	43.2	-	pF
C _{oss(eff.)}	Effective Output Capacitance	$V_{DS} = 0 \text{ V to } 480 \text{ V}, V_{GS} = 0 \text{ V}$	-	196.4	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 380 V, I _D = 11 A,	-	45	-	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	8.7	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	14.5	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	1	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-/	16.9		ns
t _r	Turn-On Rise Time	$V_{DD} = 380 \text{ V}, I_D = 11 \text{ A},$	-	16.7	- 1	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_{G} = 4.7 Ω	<i>/</i> -	49	- /	ns
t _f	Turn-Off Fall Time	(Note 4)	-	4	-	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	22	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	66	Α
V_{SD}	Drain to Source Diode Forward Voltage V _{GS} = 0 V, I _{SD} = 11 A		-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 11 A,	-	350	//-	ns
Q _{rr}	Reverse Recovery Charge $dI_F/dt = 100 \text{ A/}\mu\text{s}$		-	6	-	μС

Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. I_{AS} = 7.3 A, R_G = 25 Ω , starting T_J = 25°C.
- 3. I $_{SD}$ \leq 22 A, di/dt \leq 200 A/ μ s, V $_{DD}$ \leq 380 V, starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

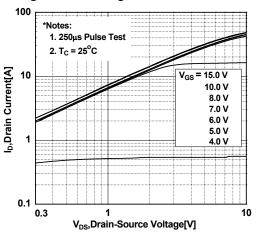


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

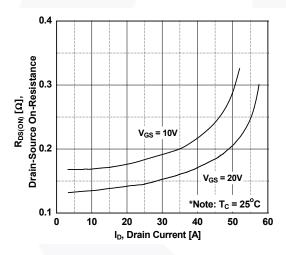


Figure 5. Capacitance Characteristics

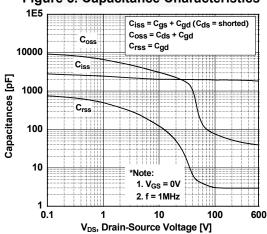


Figure 2. Transfer Characteristics

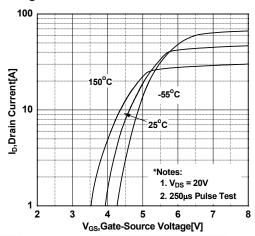


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

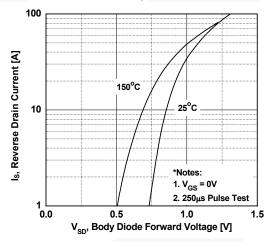
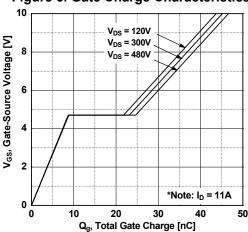


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

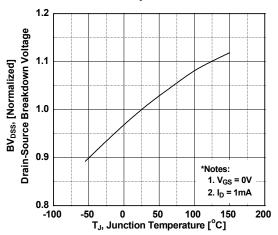


Figure 8. On-Resistance Variation vs. Temperature

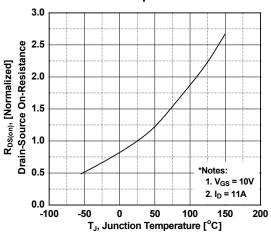


Figure 9. Maximum Safe Operating Area

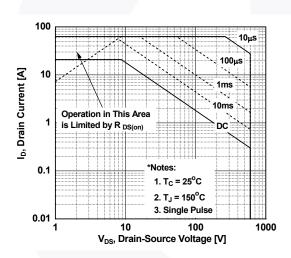


Figure 10. Maximum Drain Current vs. Case Temperature

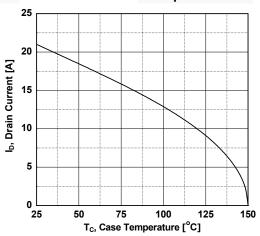
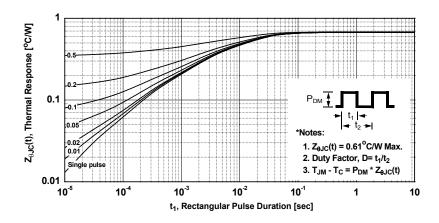


Figure 11. Transient Thermal Response Curve



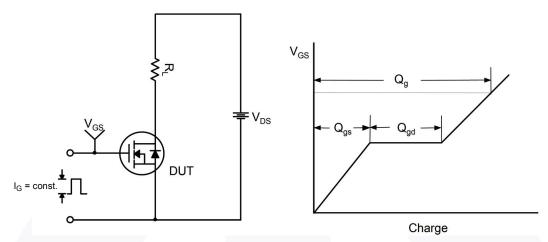


Figure 12. Gate Charge Test Circuit & Waveform

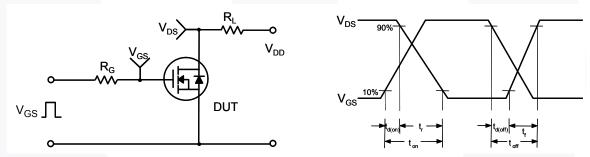


Figure 13. Resistive Switching Test Circuit & Waveforms

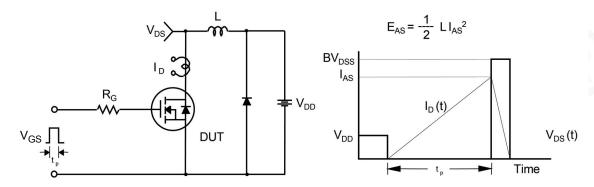


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

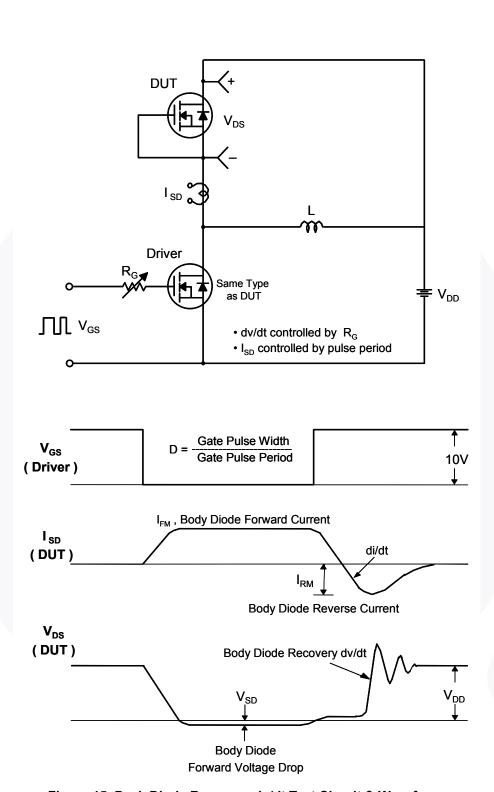
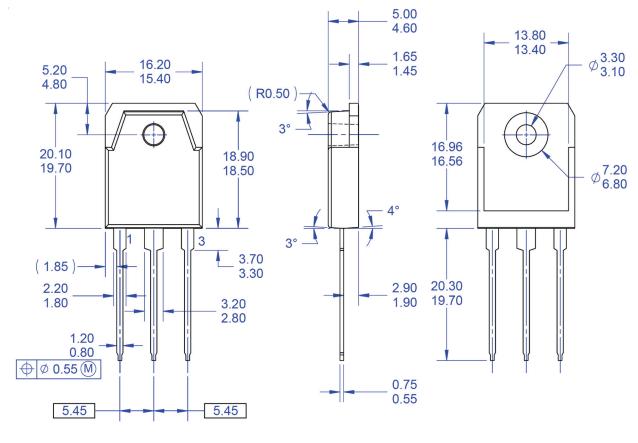
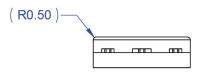


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
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Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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